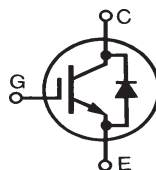


High Voltage IGBT with Diode

IXGR50N160H1

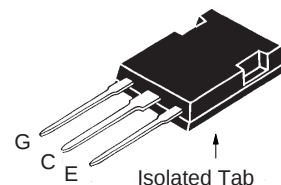
(Electrically Isolated Tab)



$$\begin{aligned} V_{CES} &= 1600V \\ I_{C110} &= 36A \\ V_{CE(sat)} &\leq 2.30V \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GE} = 1M\Omega$	1600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$, Lead RMS limit	75	A
I_{C110}	$T_C = 110^\circ\text{C}$	36	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	330	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 5\Omega$	$I_{CM} = 100$	A
(RBSOA)	Clamped Inductive Load	@ $0.8 \cdot V_{CES}$	
P_C	$T_C = 25^\circ\text{C}$	240	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
F_C	Mounting Force	20..120/4.5..27	N/lb.
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10s	260	$^\circ\text{C}$
V_{ISOL}	50/60Hz, RMS, 1 minute	2500	V~
	$I_{ISOL} \leq 1mA$ $t = 1s$	3000	V~
Weight		6	g

ISOPLUS247™



G = Gate C = Collector
E = Emitter

Features

- International Standard Package
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

Advantages

- Space Savings
- High Power Density

Applications

- Capacitor Discharge & Pulser Circuits
- AC Motor Speed Drives
- DC Servo and Robot Drives
- DC Choppers
- Uninterruptible Power Supplies (UPS)
- Switch-Mode and Resonant-Mode Power Supplies

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 1mA$, $V_{GE} = 0V$	1600		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ Note 1, $T_J = 125^\circ\text{C}$			85 μA 6 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 50A$, $V_{GE} = 15V$, Note 2 $T_J = 125^\circ\text{C}$		1.95 2.30	2.30 V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 50\text{A}$, $V_{CE} = 10\text{V}$, Note 2	18	30	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		3020	pF
C_{oes}			257	pF
C_{res}			50	pF
Q_g	$I_C = 50\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		137	nC
Q_{ge}			24	nC
Q_{gc}			57	nC
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$ $I_C = 50\text{A}$, $V_{GE} = 15\text{V}$ $R_G = 5\Omega$, $V_{CE} = 0.8 \cdot V_{CES}$		53	ns
t_r			111	ns
$t_{d(off)}$			235	ns
t_f			4400	ns
$t_{d(on)}$	Resistive Switching Times, $T_J = 125^\circ\text{C}$ $I_C = 50\text{A}$, $V_{GE} = 15\text{V}$ $R_G = 5\Omega$, $V_{CE} = 0.8 \cdot V_{CES}$		52	ns
t_r			140	ns
$t_{d(off)}$			240	ns
t_f			4600	ns
R_{thJC}			0.15	$^\circ\text{C/W}$
R_{thCS}				$^\circ\text{C/W}$

Reverse Diode (FRED)

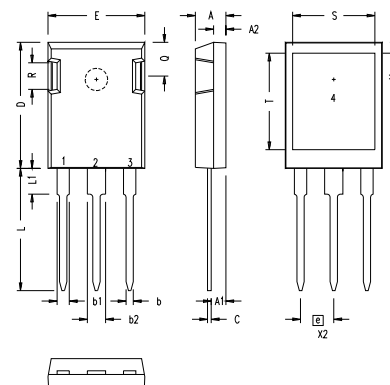
Symbol	Test Conditions (T _J = 25°C Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
V _F	I _F = 20A, V _{GE} = 0V, Note 2 T _J = 150°C			2.85 V 2.90 V
V _T	For conduction power losses only			2.10 V
r _{FO}	T _J = 150°C			40 mΩ
I _{RM}	I _F = 20A, V _{GE} = 0V, V _R = 1200V T _J = 125°C -di _F /dt = 450A/μs T _J = 125°C		23	A
t _{rr}			27	A
			230	ns
			400	ns
R _{thJC}				0.80° C/W

- Notes: 1. Device must be heatsunk for high temperature leakage current measurements to avoid thermal runaway.
2. Pulse test, $t \leq 300 \mu\text{s}$, duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

ISOPLUS247™ (IXGR) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - GATE
2 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)
4 - NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	